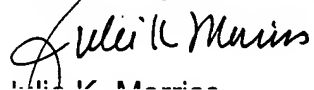


IN THE ABSTRACT:

Please delete the Abstract as originally filed in the International Application, including the "Title" and "[Figure 6F]" designation on that same page, and substitute therefor the following:

A method for forming a modified semiconductor having a number of band gaps[.]. ~~The first step involves providing a semiconductor having a surface and a quantum region which emits photons in response to electrical or optical stimulation, the quantum region having an original band gap and being disposed under the surface[.].~~ ~~The next step involves~~ and applying a number of layers of a number of materials to a number of selected regions of the surface, the materials being adapted to cause, upon thermal annealing, a number of different degrees of intermixing in a number of portions of the quantum region disposed immediately below each of the selected regions of the surface. The layers of materials can be applied in a dot or line pattern, or both, to increase the plurality of band gap tuning. ~~The next step involves~~ method includes thermally annealing the layers to the surface ~~such that the layers cause a number of degrees of intermixing in the different portions of said quantum region thereby shifting the original band gaps of those portions. These steps~~ The methods result in a modified semiconductor which exhibits a number of different band gaps in a number of portions of the quantum region depending upon the positioning of the layers of materials on the surface immediately above the respective portions of the quantum region.

Respectfully submitted,

A handwritten signature in cursive script, appearing to read "Julie K. Morriss".

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